

FORM PTO-1449 (Rev. 2-32)		U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
<p style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p>(Use several sheets if necessary)</p>		05-720-US1	10/559,979	
		Applicant: Kouvetakis, et al.		
		Filing Date: December 8, 2005	Group: 2814	

U.S. PATENT DOCUMENTS
ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /SR/

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
/SR/	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.			
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.			
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.			
	3.	6,911,084	June 28, 2005	Kouvetakis, et al.			
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	8.	6,410,434	June 25, 2002	Mani			
	8.	6,723,621	April 20, 2004	Cordone, et al.			
V	10.	6,897,471	May 24, 2005	Soref, et al.			
/SR/	11.	6,441,716	August 27, 2002	Doppalapudi, et al.			

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Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation
							<input type="checkbox"/> Yes <input type="checkbox"/> No

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/SR/	12.	WO 2005/001902	January 6, 2005	PCT				
	13.	WO 2004/114368	December 29, 2004	PCT				
	14.	WO 2005/015609	February 17, 2005	PCT				
	15.	WO 2003/033781	April 24, 2003	PCT				
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				
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Applicant: Kouvetakis, et al.				
Filing Date: December 8, 2005		Group: 2814		

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COMMONLY OWNED CO-PENDING APPLICATIONS

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		December 8, 2005	2814

/SR/	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
/SR/	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,981, Filed on September 5, 2006 (Projected Publication date is January 11, 2007).

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /SR/

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